

MiniSKiiP® 2

Sixpack

SKiiP 24AC12T4V1

Features*

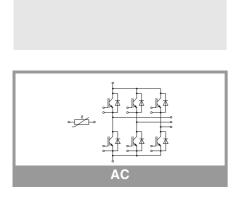
- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

Typical Applications

- Inverter up to 22 kVA
- Typical motor power 11 kW

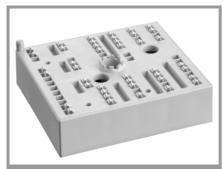
Remarks

- V_{CEsat}, V_F = chip level value
- Case temp. limited to $T_C = 125$ °C max. (for baseplateless modules $T_C = T_S$)
- product rel. results valid for T_j ≤150 (recomm. T_{op} = -40 ... +150°C)



Absolute	Maximum Rating	s			
Symbol	Conditions		Values	Unit	
Inverter -	IGBT		•		
V _{CES}	T _j = 25 °C		1200	V	
Ic	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	52	Α	
	T _j = 175 °C	T _s = 70 °C	43	Α	
Ic	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	59	Α	
	T _j = 175 °C	T _s = 70 °C	48	Α	
I _{Cnom}			35	Α	
I _{CRM}			105	Α	
V _{GES}			-20 20	V	
t _{psc}	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T _j = 150 °C	10	μs	
Tj		1	-40 175	°C	
Inverse -	Diode			<u> </u>	
V_{RRM}	T _j = 25 °C		1200	V	
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	44	Α	
	T _j = 175 °C	T _s = 70 °C	35	Α	
l _F	λ_{paste} =2.5 W/(mK) T _j = 175 °C	T _s = 25 °C	49	Α	
		T _s = 70 °C	40	Α	
I _{FRM}			105	Α	
I _{FSM}	$t_p = 10 \text{ ms}, \sin 180^\circ$	°, T _j = 150 °C	170	Α	
Tj			-40 175	°C	
Module				•	
I _{t(RMS)}	T _{terminal} = 80 °C, 20	A per spring	100	Α	
T _{stg}	module without TIM	Л	-40 125	°C	
V _{isol}	AC sinus 50 Hz, t =	= 1 min	2500		

Characteristics									
Symbol	Conditions	min.	typ.	max.	Unit				
Inverter - IGBT									
V _{CE(sat)}	$I_{\rm C} = 35 {\rm A}$	T _j = 25 °C		1.85	2.10	V			
	V _{GE} = 15 V chiplevel	T _j = 150 °C		2.25	2.45	V			
V _{CE0}	chiplevel	T _j = 25 °C		0.80	0.90	V			
	Chipievei	T _j = 150 °C		0.70	0.80	V			
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		30	34	$m\Omega$			
	chiplevel	T _j = 150 °C		44	47	mΩ			
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1$ m.	A	5	5.8	6.5	V			
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = 12$	00 V, T _j = 25 °C			1	mA			
C _{ies}	Vor - 25 V	f = 1 MHz		1.95		nF			
Coes		f = 1 MHz		0.16		nF			
C _{res}	VGE - O V	f = 1 MHz		0.12		nF			
Q_{G}	V _{GE} = - 8 V+ 15 V			200		nC			
R _{Gint}	T _j = 25 °C			0		Ω			
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		21		ns			
t _r	I _C = 35 A	T _j = 150 °C		31		ns			
Eon	$R_{G \text{ on}} = 15 \Omega$ $R_{G \text{ off}} = 15 \Omega$	T _j = 150 °C		3.7		mJ			
t _{d(off)}	$di/dt_{on} = 1300 \text{ A/}\mu\text{s}$	T _j = 150 °C		310		ns			
t _f		T _j = 150 °C		63		ns			
E _{off}	V _{GE} = +15/-15 V	T _j = 150 °C	3			mJ			
R _{th(j-s)}	per IGBT, λ _{paste} =0.8	3 W/(mK)		0.85		K/W			
R _{th(j-s)}	per IGBT, λ _{paste} =2.5	5 W/(mK)		0.69		K/W			



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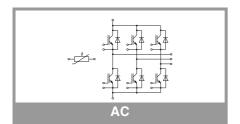
Typical Applications

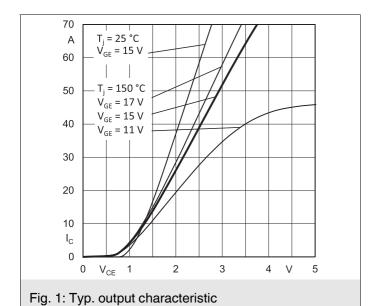
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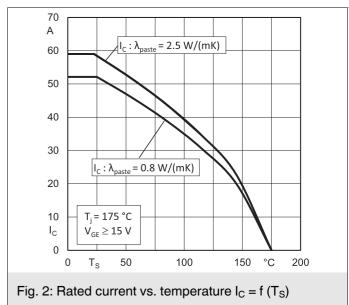
Remarks

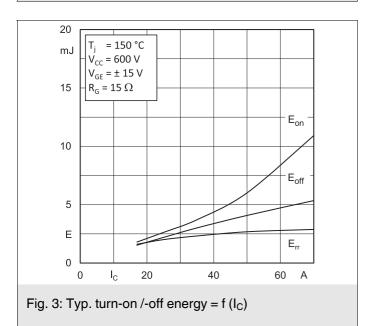
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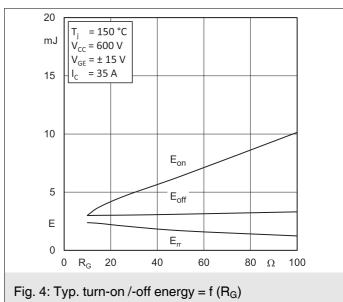
Characte	eristics					
Symbol	Conditions		min.	typ.	max.	Unit
Inverse -	Diode					•
$V_F = V_{EC}$	$I_F = 35 \text{ A}$	T _j = 25 °C		2.30	2.62	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.29	2.62	V
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
	ompiever	T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		29	32	mΩ
	Chipievei	T _j = 150 °C		40	43	mΩ
I _{RRM}	$I_F = 35 A$	T _j = 150 °C		38		Α
Q _{rr}	di/dt _{off} = 1400 A/μs V _{GE} = +15/-15 V	T _j = 150 °C		6.2		μC
E _{rr}	$V_{CC} = 600 \text{ V}$	T _j = 150 °C		2.3		mJ
R _{th(j-s)}	per Diode, λ _{paste} =0.		1.2		K/W	
R _{th(j-s)}	per Diode, λ _{paste} =2.		1		K/W	
Module						
L _{CE}				-		nΗ
Ms	to heat sink		2		2.5	Nm
W				55		g
Temperat	ture Sensor					
R ₁₀₀	T _r =100°C (R ₂₅ =100		1670 ± 3%		Ω	
R _(T)	$R_{(T)}$ =1000 Ω [1+A(T-1000), A = 7.635*10 ⁻³ °C-1000] B = 1.731*10 ⁻⁵ °C-2	-25°C)+B(T-25°C) ²]				

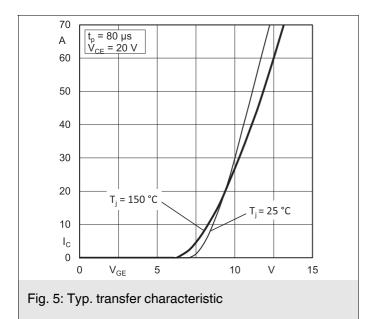


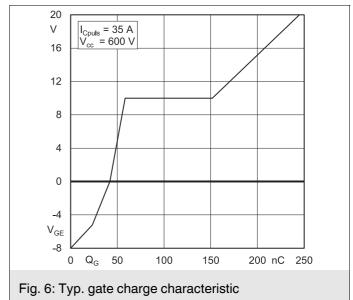


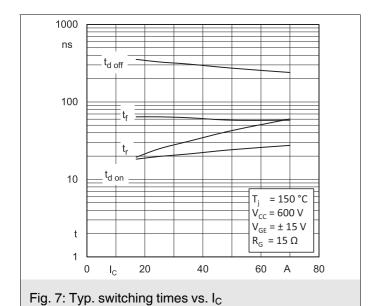


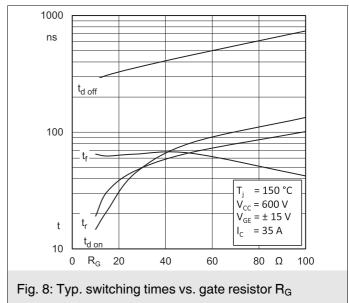


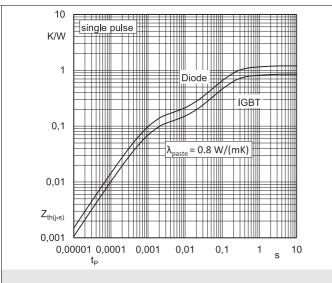




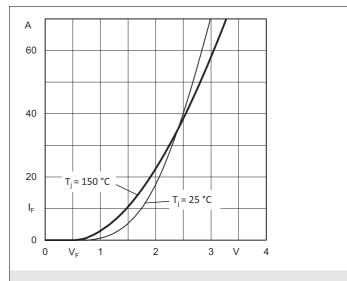


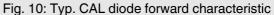


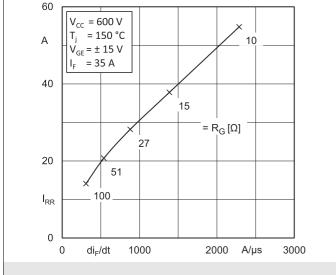


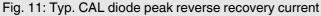












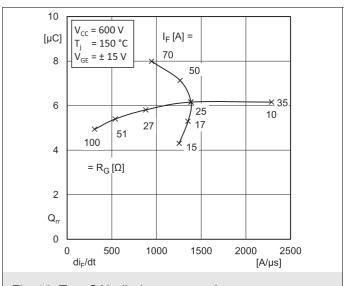
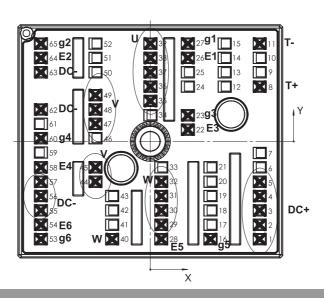


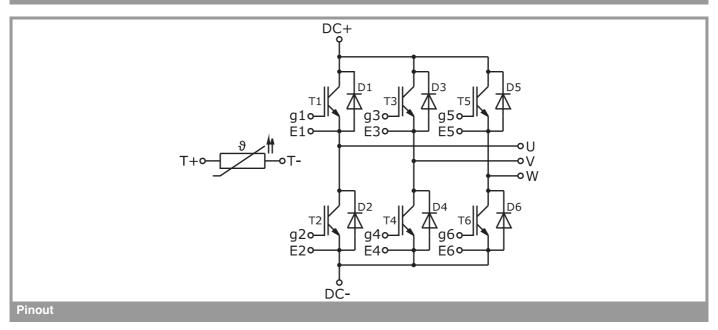
Fig. 12: Typ. CAL diode recovery charge

Pin out											
Pin	X	Υ	Function	Pin	X	Υ	Function	Pin	X	Υ	Function
1	24,38	-21,80	DC+	23	8,38	5,80	g3	45	-12,23	-5,80	V
2	24,38	-18,60	DC+	24	8,38	12,20		46	-12,23	0,70	
3	24,38	-15,40	DC+	25	8,38	15,40		47	-12,23	3,90	V
4	24,38	-12,20	DC+	26	8,38	18,60	E1	48	-12,23		V
5	24,38	-9,00	DC+	27	8,38	21,80	g1	49	-12,23	10,30	V
6	24,38	-5,80		28	2,46	-21,80	E5	50	-12,23	15,40	
7	24,38	-2,60		29	2,46	-18,60	W	51	-12,23	18,60	
8	24,38	12,20	T+	30	2,46	-15,40	W	52	-12,23		
9	24,38	15,40		31	2,46	-12,20	W	53	-24,38	-21,80	g6
10	24,38	18,60		32	2,46	-9,00	W	54	-24,38	-18,60	E6
11	24,38	21,80	T-	33	2,46	-5,80		55	-24,38	-15,40	DC-
12	16,58	12,20		34	0,03	5,80		56	-24,38	-12,20	DC-
13	16,58	15,40		35	0,03	9,00	U	57	-24,38	-9,00	DC-
14	16,58	18,60		36	0,03	12,20	U	58	-24,38	-5,80	E4
15	16,58	21,80		37	0,03	15,40	U	59	-24,38	-2,50	
16	13,42	-21,80	g5	38	0,03	18,60	U	60	-24,38	0,70	g4
17	13,42	-18,60		39	0,03	21,80	U	61	-24,38	3,90	
18	13,42	-15,40		40	-8,51	-21,80	W	62	-24,38	7,10	DC-
19	13,42	-12,20		41	-8,51	-18,60		63	-24,38	15,40	DC-
20	13,42	-9,00		42	-8,51	-15,40		64	-24,38	18,60	E2
21	13,42	-5,80		43	-8,51	-12,20		65	-24,38	21,80	g2
22	8,38	2,60	E3	44	-12,23	-9,00	V				

all values in mm



Pinout and Dimensions



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

*IMPORTANT INFORMATION AND WARNINGS

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